UNT Nanofabrication Cleanroom (NFCR)

Sepertem,2016

- Capacity update

Cleanroom Capacity Update

- Ebeam Lithography: JEOL 7001 SEM & XPG pattern generator
- Maskless photolithography: Heidelberg Laser writer
- Trovato OLED system
- RIE etching capacity
- User EBL sample from Ben
- 1st external user application

Ebeam Lithography: JEOL 7001 SEM & XPG pattern generator

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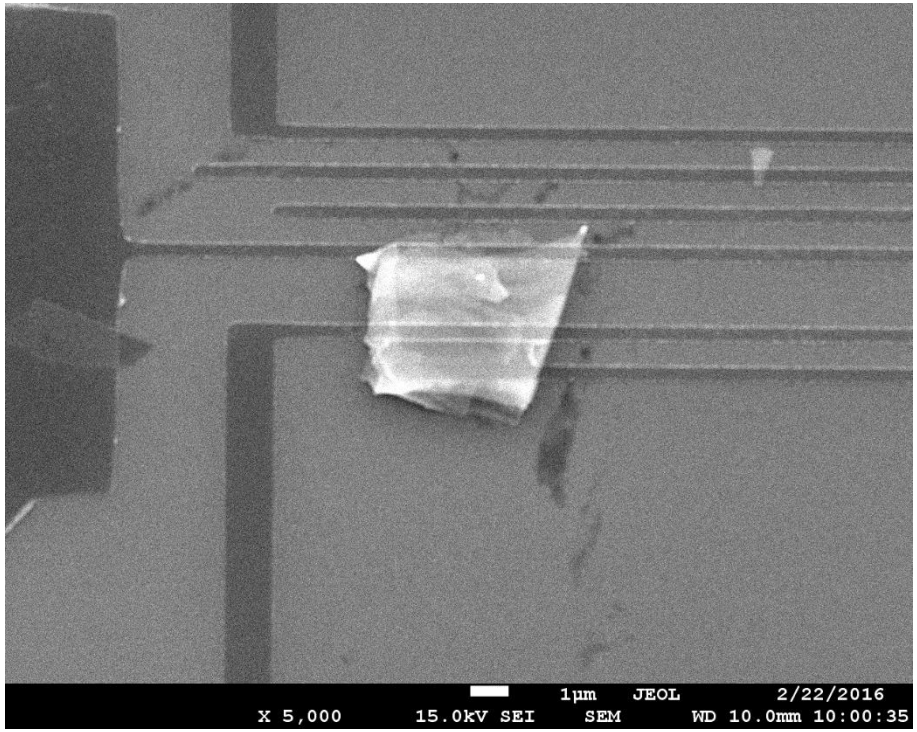
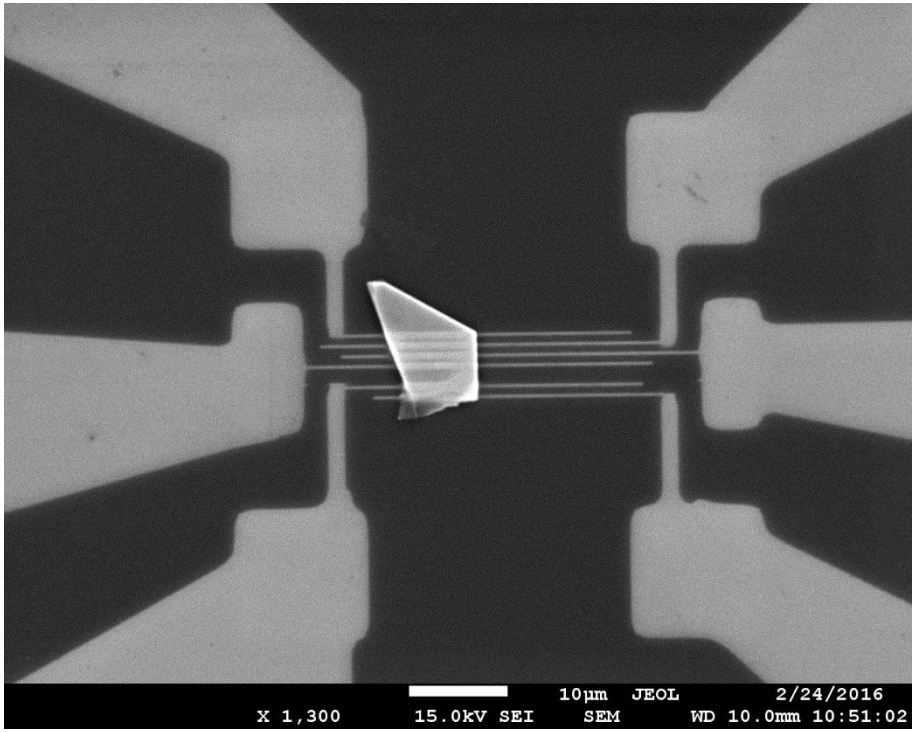
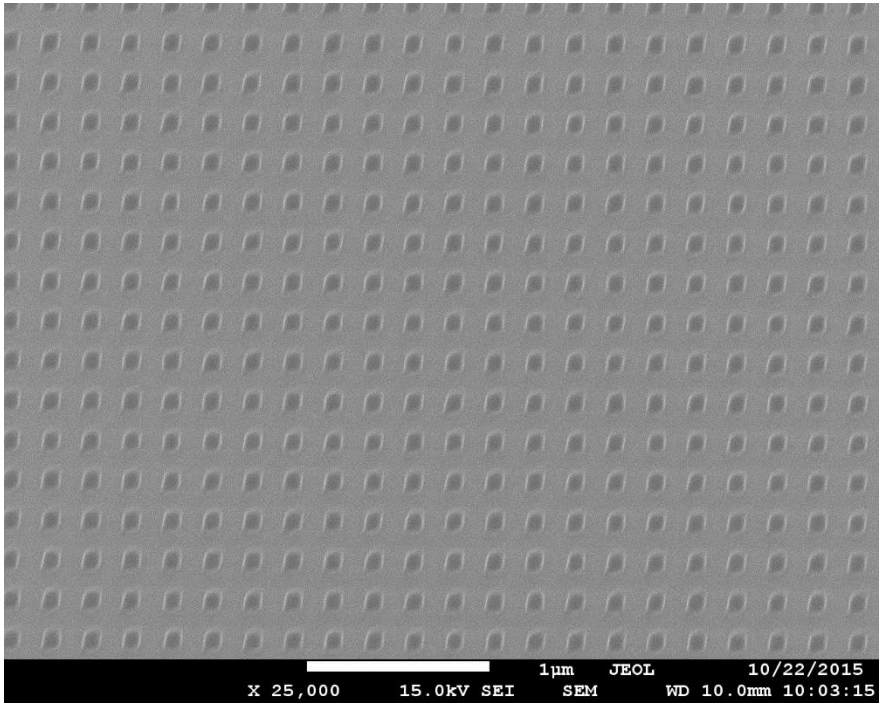
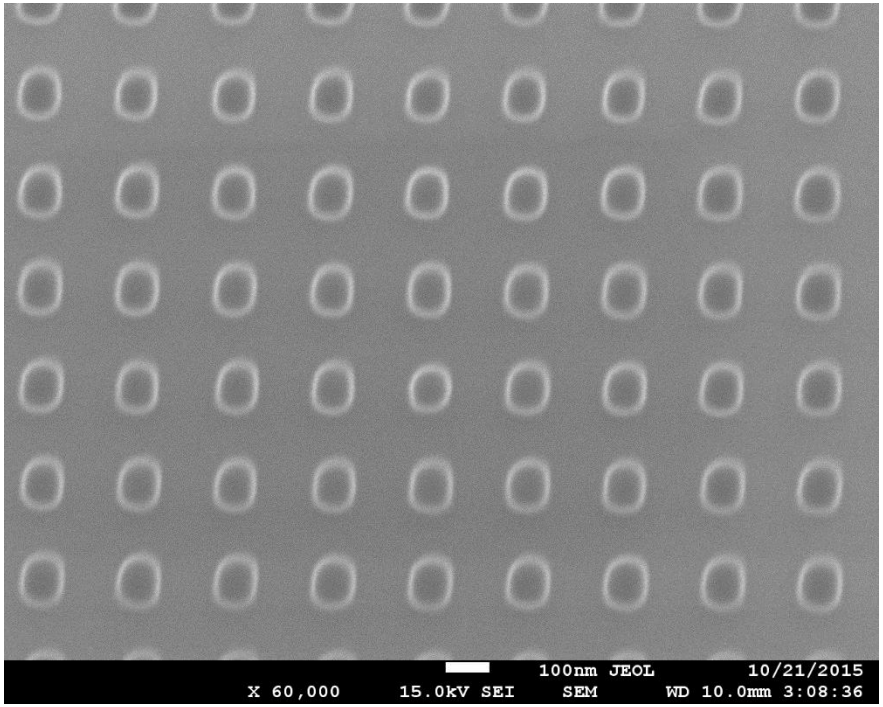




Contact patterns on <10 um MoTe2 flakes.
After liftoff (left) and after development (right)

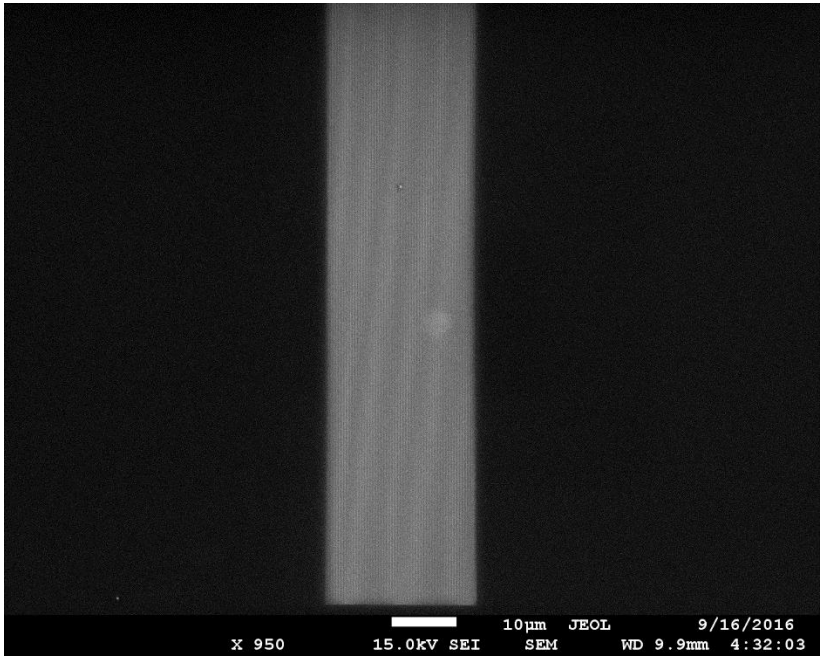
Ebeam Lithography: JEOL 7001 SEM & XPG pattern generator

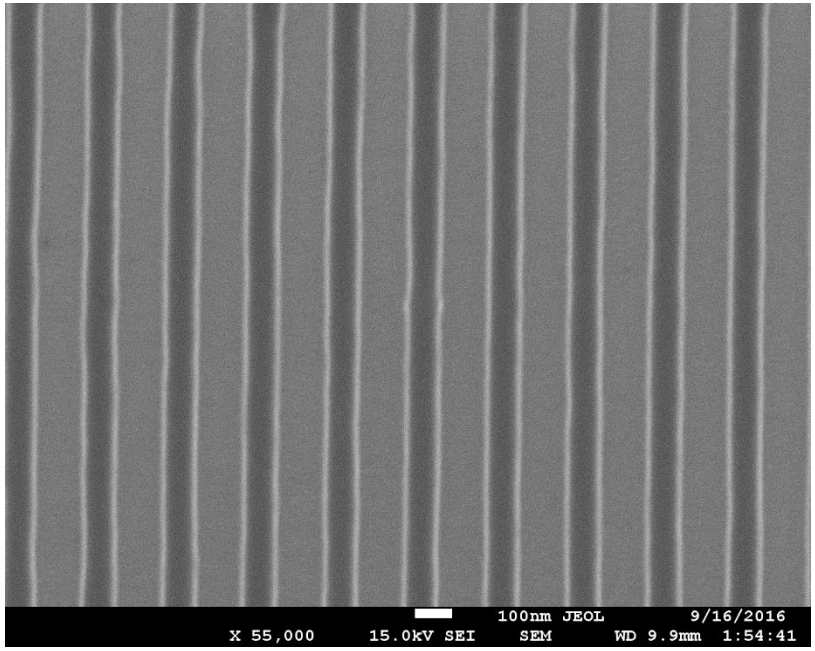




Fishnet pattern after development.
Field size 100 um and 120x120 nm grids

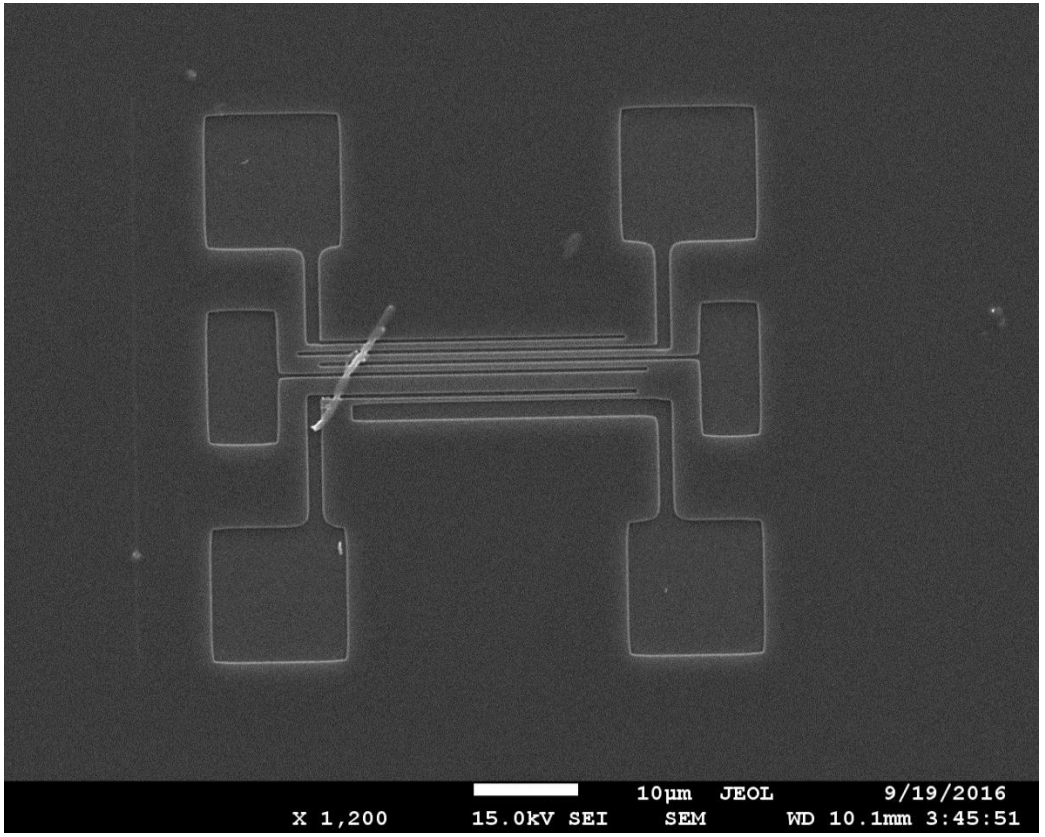
Ebeam Lithography: JEOL 7001 SEM & XPG pattern generator





Line patterns for graphene etching.
Field size 100 um and 100 nm lines and 100 nm gaps.

Ebeam Lithography: JEOL 7001 SEM & XPG pattern generator

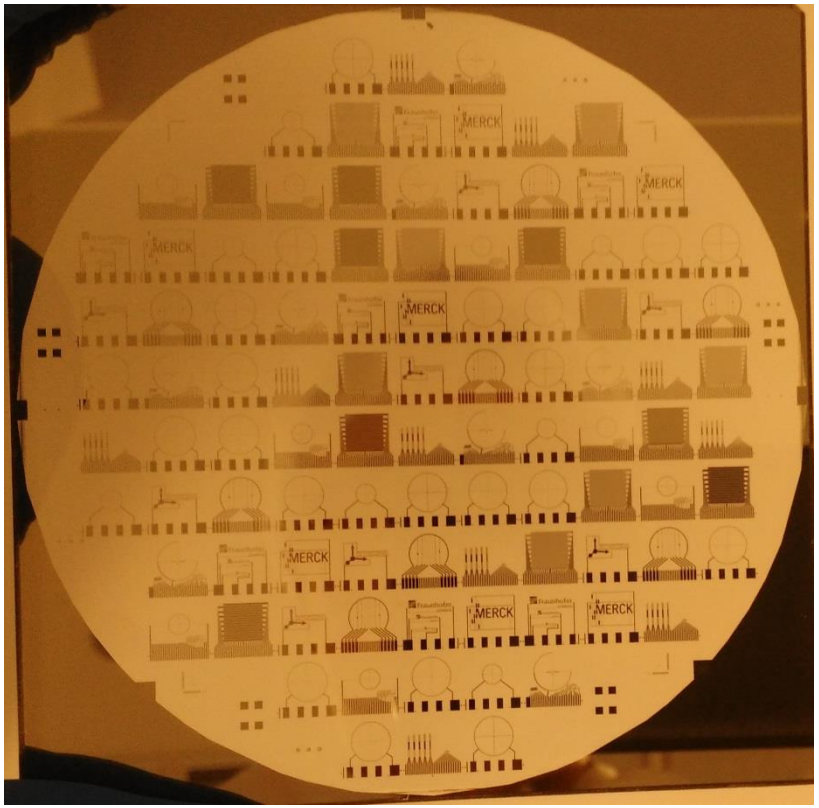


Carbon nanotube contact patterning.

Maskless photolithography: Heidelberg Laser writer
Chemical processing stations

Maskless photolithography: Heidelberg Laser writer Photomask writing service

- Resolution >=1um and >=10 um features
- 4 mm writer head for high resolution and 40 mm write head for fast writing



4”x4” Photomasks writing service

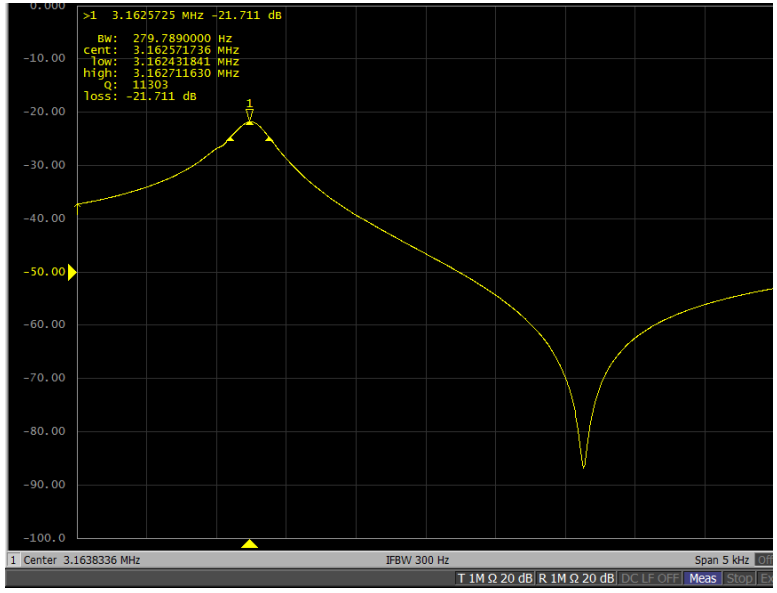
Maskless photolithography: Heidelberg Laser writer Direct write pattern service

- Resolution >=1um and >=10 um features
- 4 mm writer head for high resolution and 40 mm write head for fast writing

Ag Contact pattern on 1 inch Si wafer

Maskless photolithography: Heidelberg Laser writer Example

- frequency response curve of LGS (Langasite) crystal material for viscosity measurement using BAW (bulk acoustic wave) resonator technique



Trovato OLED deposition system

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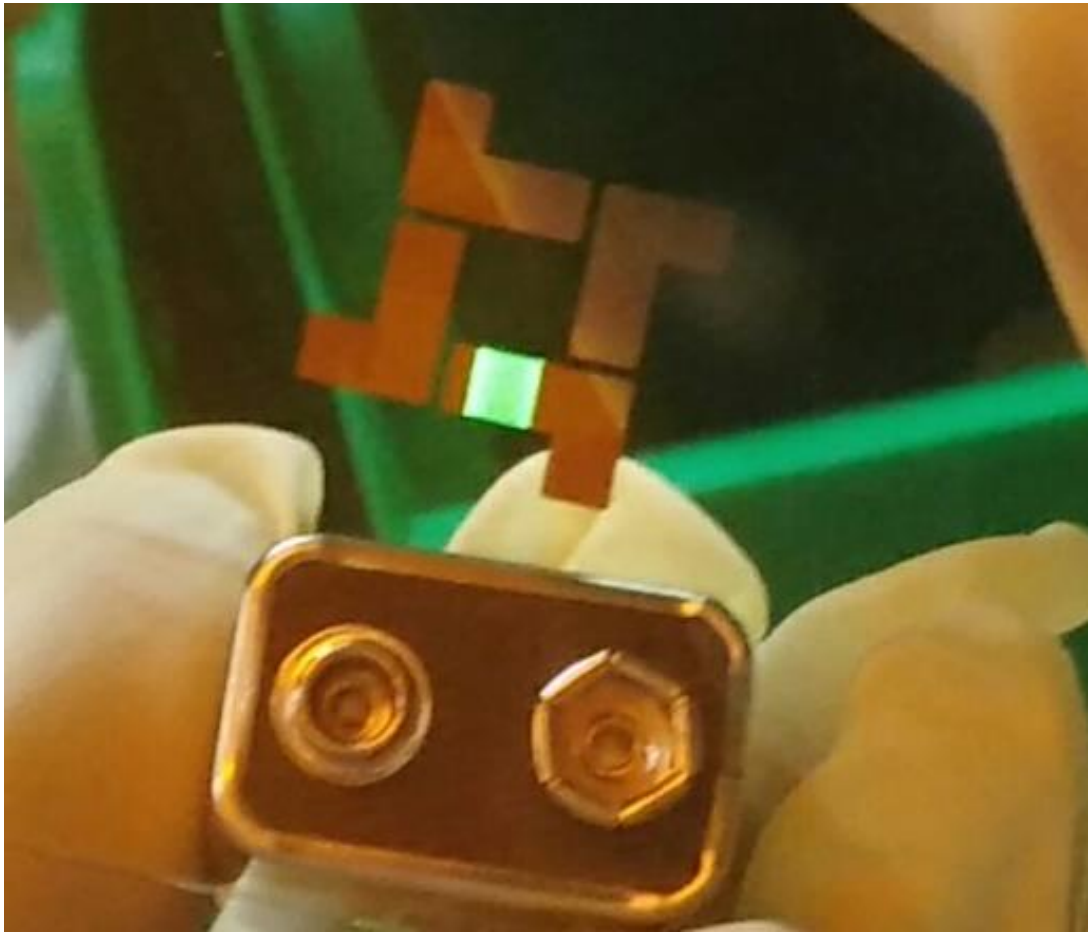
Al/LiF/AlQ/MBT/ITO

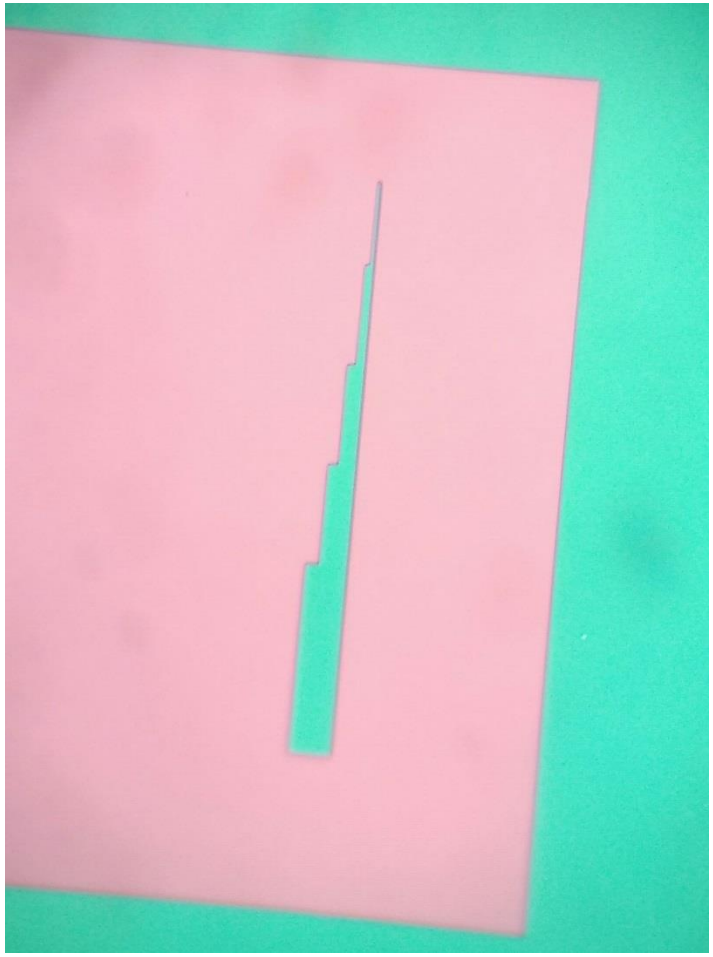
OLED fabrication



Reactive Ion Etching

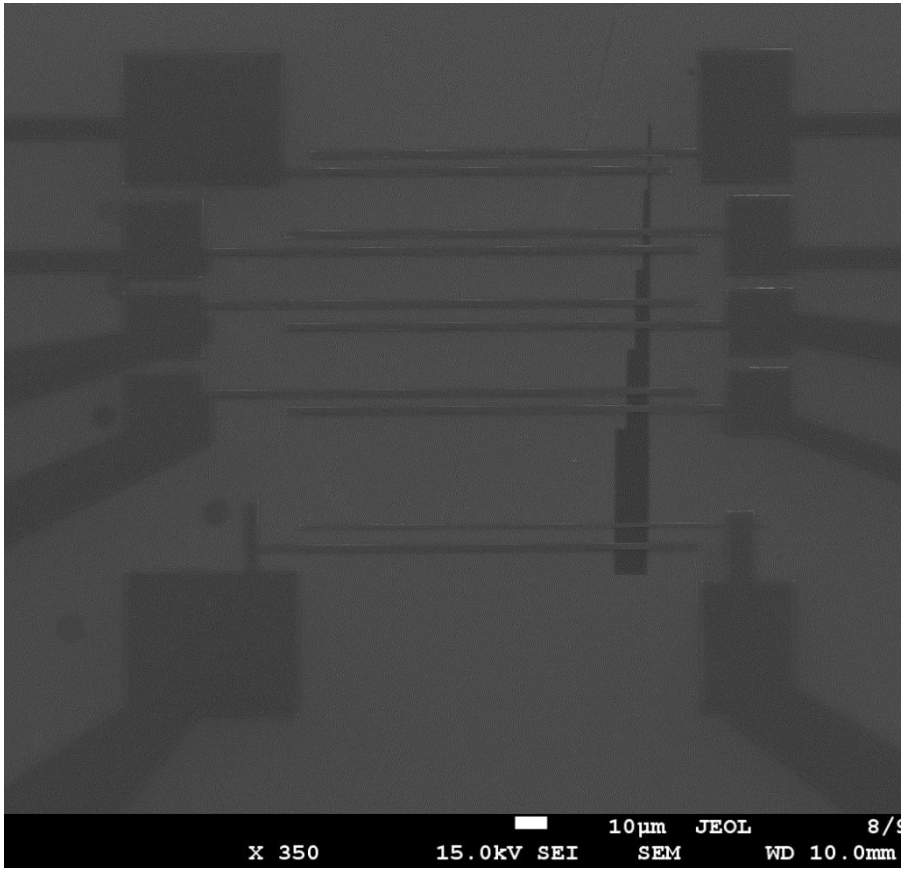
Reactive Ion Etching

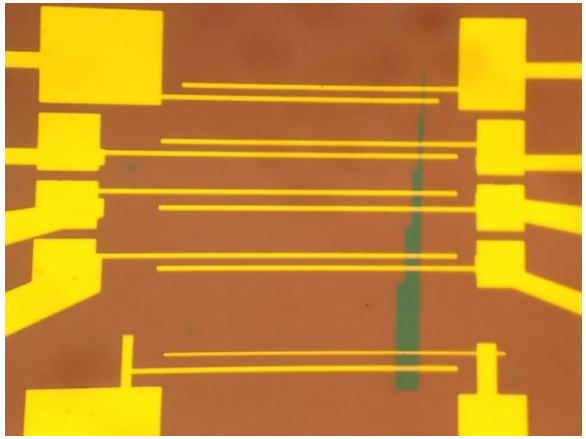
- Etching MoS_2/SiO_2 thin film to Stair shape pattern.
- Blue area is MoS_2. pink area is SiO_2 without MoS_2
- The widths for each stair are: 0.5um, 1.2um,3um, 6um, 11um



Reactive Ion Etching & Contact patterning

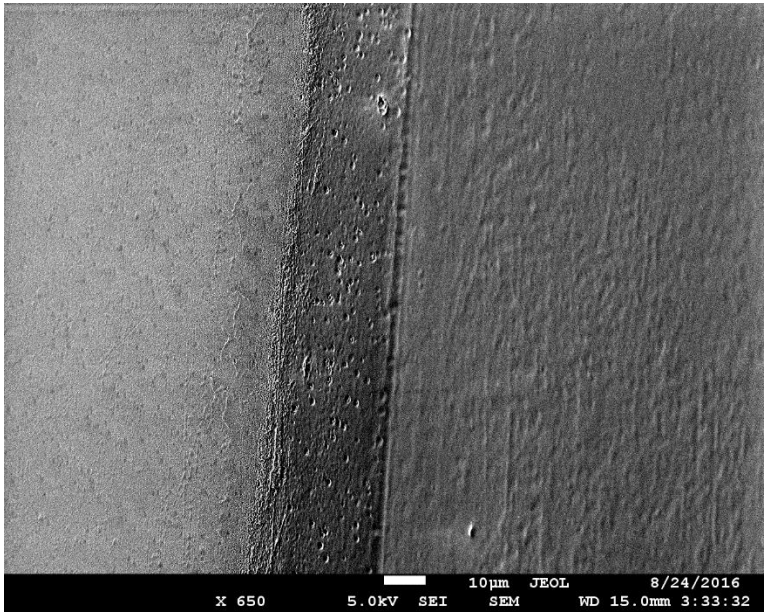
- Patterning the Ag contact on top of the etched MoS2 stairs
- Ebeam evaporator for the Ag contacts

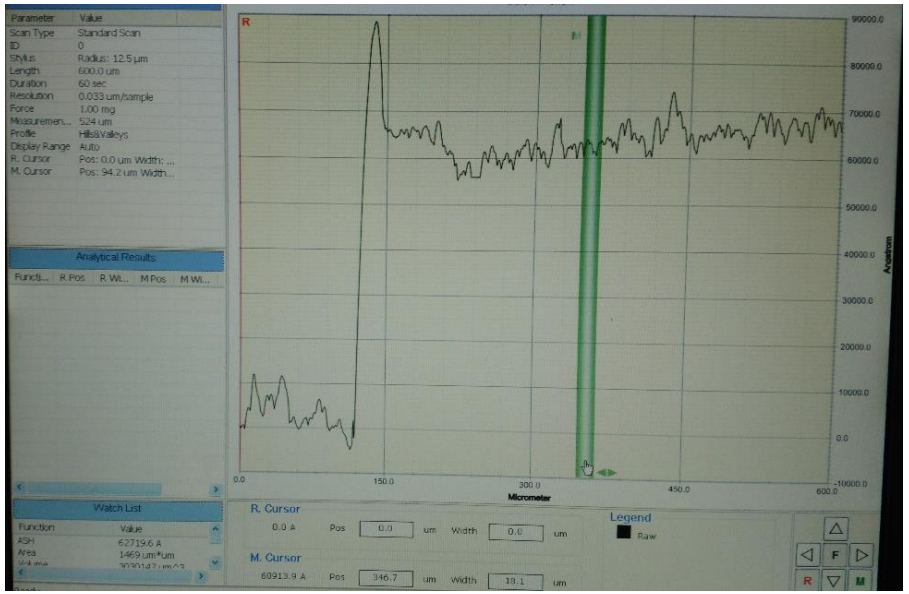




Reactive Ion Etching

- Etching quartz slide to depth of 6 um or more





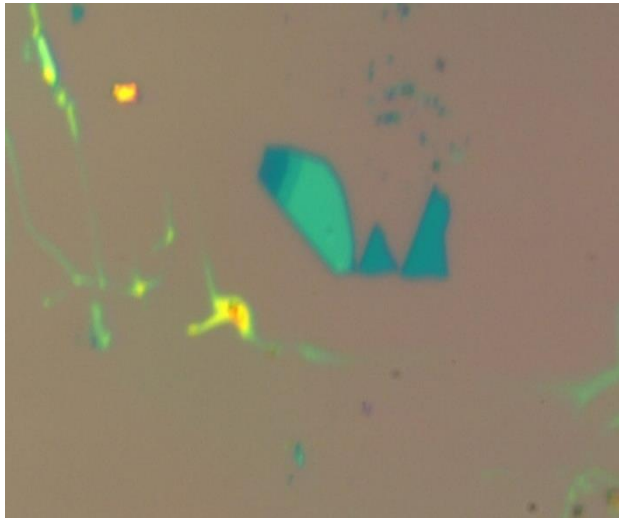
Titled cross section

Back-gated FETs from MoTe2 flakes

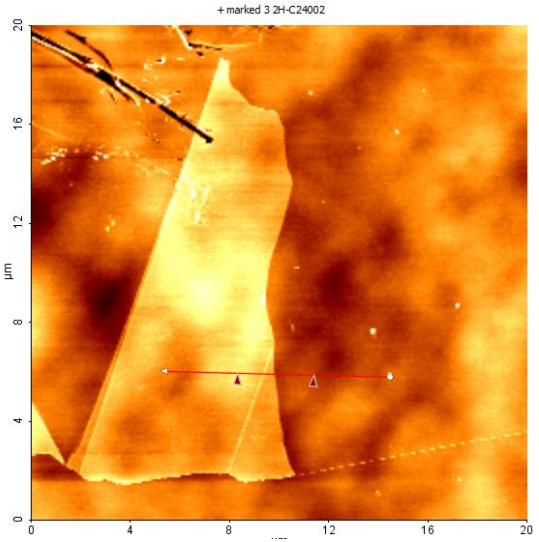
Ben Sirota

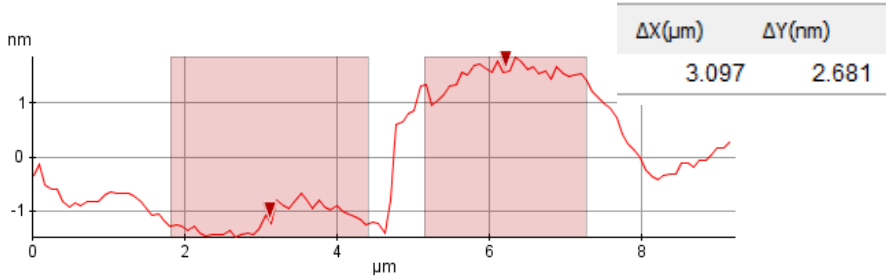
Materials Science and Engineering

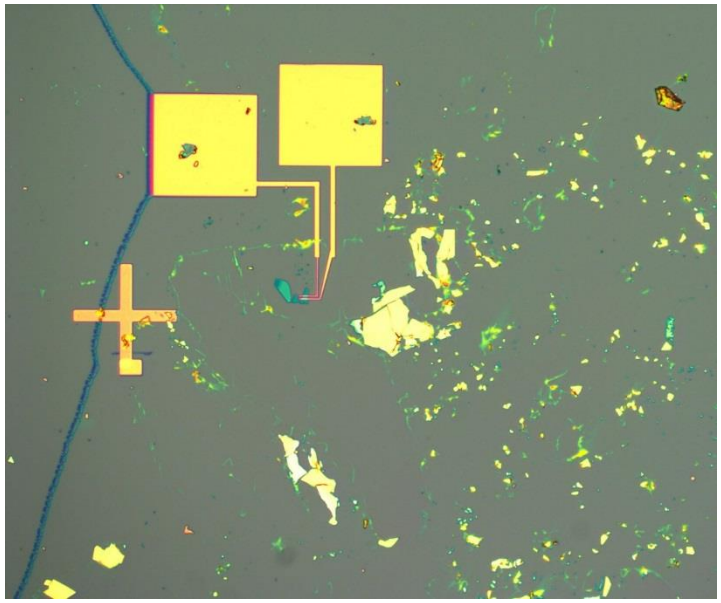
MoTe2 flakes were exfoliated from bulk crystals on silicon substrates with a 300 nm SiO2 layer. Flakes were identified using optical microscope.

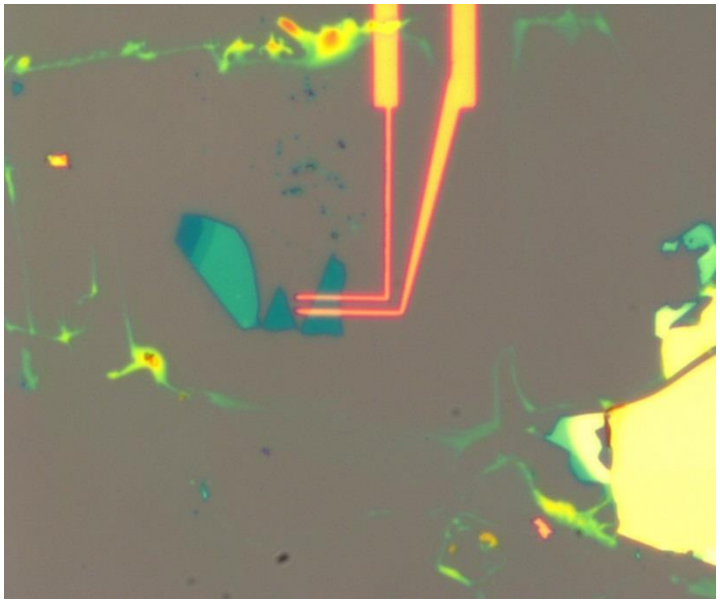


Flake size and thickness was confirmed using AFM. In this case, the thickness was measured as 2.681 nm which is about 3 atomic layers.

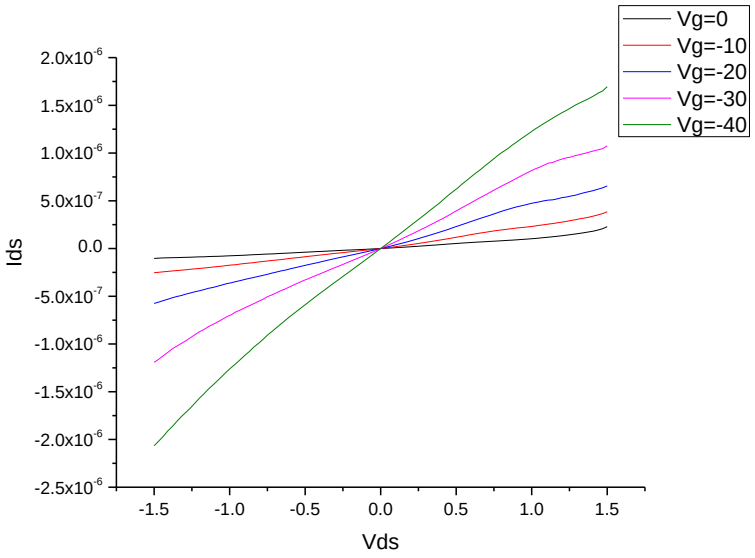




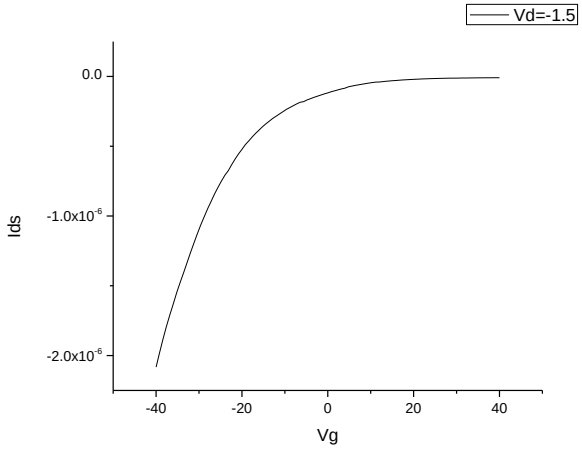




Electrical contacts where designed and written using electron beam lithography. Ti/Au (5/20 nm) metal contacts where deposited by electron-beam evaporation and lift-off. The two deposited contacts form the source and drain while the silicon substrate is used as the gate electrode. Finally, the SiO2 insulative layer acts as a dielectric layer. Therefore these devices are known as back-gated field effect transistors.



2H-C24
3-2
+M4



Electrical properties where measured using a voltmeter and probe station. The exfoliated flakes demonstrate very responsive FET properties with a high on/off ratio. The MoTe2 flake exhibits p-type semiconductor behavior.

1st External user application

KubOS, inc. testing their mini Satellite module with Oerlikon High vacuum chamber.